DESCRIPTION

THE Hynix HY57V161610D is a 16,777,216-bits CMOS Synchronous DRAM, ideally suited for the Mobile applications which require low power consumption and industrial temperature range. HY57V161610D is organized as 2banks of 524,288x16.

HY57V161610D is offering fully synchronous operation referenced to a positive edge clock. All inputs and outputs are synchronized with the rising edge of the clock input. The data paths are internally pipelined to achieve very high bandwidth. All input and output voltage levels are compatible with LVTTL.

Programmable options include the length of pipeline (Read latency of 1,2 or 3), the number of consecutive read or write cycles initiated by a single control command (Burst length of 1,2,4,8 or full page), and the burst count sequence(sequential or interleave). A burst of read or write cycles in progress can be terminated by a burst terminate command or can be interrupted and replaced by a new burst read or write command on any cycle. (This pipeline design is not restricted by a `2N` rule.)

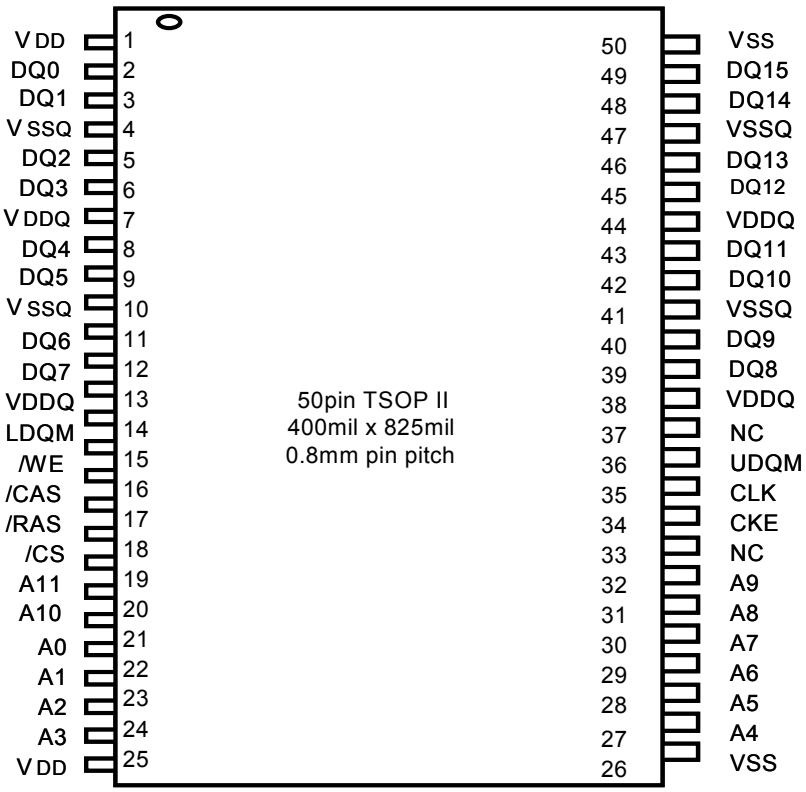
FEATURES

- Single 3.0V to 3.6V power supply[Note1)]
- All device pins are compatible with LVTTL interface
- JEDEC standard 400mil 50pin TSOP-II with 0.8mm of pin pitch
- All inputs and outputs referenced to positive edge of system clock
- Data mask function by UDQM/LDQM
- Internal two banks operation
- Auto refresh and self refresh
- 4096 refresh cycles / 64ms
- Programmable Burst Length and Burst Type
  - 1, 2, 4, 8 and Full Page for Sequence Burst
  - 1, 2, 4 and 8 for Interleave Burst
- Programmable $\overline{\text{CAS}}$ Latency ; 1, 2, 3 Clocks

ORDERING INFORMATION

Part No.	Clock Frequency	Organization	Interface	Package
HY57V161610DTC-55I	183MHz	2Banks x 512Kbits x 16	LVTTL	400mil 50pin TSOP II
HY57V161610DTC-6I	166MHz			
HY57V161610DTC-7I	143MHz			
HY57V161610DTC-10I	100MHz			

PIN CONFIGURATION



PIN DESCRIPTION

PIN	PIN NAME	DESCRIPTION
CLK	Clock	The system clock input. All other inputs are referenced to the SDRAM on the rising edge of CLK.
CKE	Clock Enable	Controls internal clock signal and when deactivated, the SDRAM will be one of the states among power down, suspend or self refresh.
$\overline{CS}$	Chip Select	Command input enable or mask except CLK, CKE and DQM
BA	Bank Address	Select either one of banks during both $\overline{RAS}$ and $\overline{CAS}$ activity.
A0 ~ A10	Address	Row Address : RA0 ~ RA10, Column Address : CA0 ~ CA7 Auto-precharge flag : A10
$\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$	Row Address Strobe, Column Address Strobe, Write Enable	$\overline{RAS}$, $\overline{CAS}$ and $\overline{WE}$ define the operation. Refer function truth table for details
LDQM, UDQM	Data Input/Output Mask	DQM control output buffer in read mode and mask input data in write mode
DQ0 ~ DQ15	Data Input/Output	Multiplexed data input / output pin
VDD/VSS	Power Supply/Ground	Power supply for internal circuit and input buffer
VDDQ/VSSQ	Data Output Power/Ground	Power supply for DQ
NC	No Connection	No connection

FUNCTIONAL BLOCK DIAGRAM

1Mx16 Synchronous DRAM